

Silicon PNP Power Transistors

2SA765

DESCRIPTION

- With TO-66 package
- Low collector saturation voltage

APPLICATIONS

- Designed for general-purpose power amplifier and applications

PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |

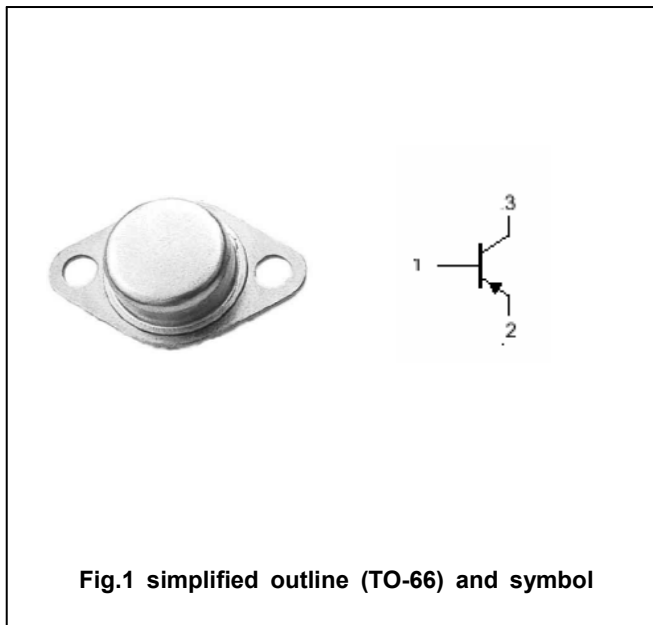


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|---------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -80 | V |
| V _{CEO} | Collector-emitter voltage | Open base | -80 | V |
| V _{EBO} | Emitter-base voltage | Open collector | -6 | V |
| I _C | Collector current | | -6 | A |
| P _C | Collector power dissipation | T _C =25□ | 40 | W |
| T _j | Junction temperature | | 150 | □ |
| T _{stg} | Storage temperature | | -55~150 | □ |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-10mA ; I _B =0 | -80 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =-1mA ; I _E =0 | -80 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-4A; I _B =-0.4A | | | -1.5 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =-4A; I _B =-0.4A | | | -2.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-80V; I _E =0 | | | -10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =-6V; I _C =0 | | | -10 | μA |
| h _{FE} | DC current gain | I _C =-1A ; V _{CE} =-4V | 50 | | | |
| f _T | Transition frequency | I _C =-0.5A ; V _{CE} =-12V | | 10 | | MHz |

PACKAGE OUTLINE



Fig.2 outline dimensions